

## DESCRIPTION

The MX40P08 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as -4.5V. This device is suitable for use as a wide variety of applications.

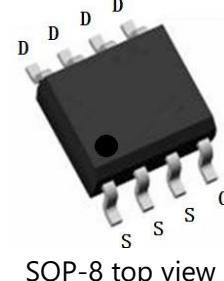
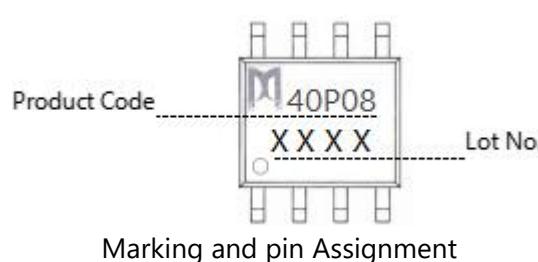
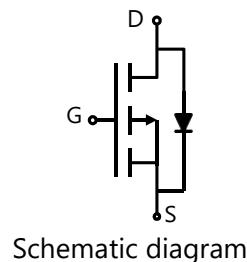
## GENERAL FEATURES

- $V_{DS} = -40V$ ,  $I_D = -8A$
- $R_{DS(ON)}(\text{Typ.}) = 21\text{m}\Omega$  @  $V_{GS} = -4.5V$
- $R_{DS(ON)}(\text{Typ.}) = 16\text{m}\Omega$  @  $V_{GS} = -10V$
- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

## APPLICATION

- DC-DC converter
- Load switch
- Power management

## PINOUT



## ORDERING INFORMATION

Part Number	Storage Temperature	Package	Devices Per Reel
MX40P08	-55°C to 150°C	SOP-8	2500

## ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	-40	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous( $T_C = 25^\circ C$ )	$I_D$	-8	A
Drain Current-Continuous( $T_C = 100^\circ C$ )		-5	
Pulsed Drain Current <sup>(Note1)</sup>	$I_{DM}$	-32	A
Maximum Power Dissipation( $T_C = 25^\circ C$ )	$P_D$	3	W
Maximum Power Dissipation( $T_C = 100^\circ C$ )		1.2	
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	°C

## THERMAL RESISTANCE

Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	42	°C/W
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Note 1. Repetitive Rating: Pulse width limited by maximum junction temperature.


**ELECTRICAL CHARACTERISTICS**( $T_A=25^\circ\text{C}$  unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
<b>On/Off Characteristics</b>						
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=-250\mu\text{A}$	-40	-	-	V
Zero Gate Voltage Drain Current	$I_{\text{DSS}}$	$V_{\text{DS}}=-40\text{V}, V_{\text{GS}}=0\text{V}$	-	-	-1	$\mu\text{A}$
Gate-Body Leakage Current	$I_{\text{GSS}}$	$V_{\text{GS}}=\pm 20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	$\pm 100$	nA
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=-250\mu\text{A}$	-1.1	-1.7	-2.5	V
Drain-Source On-State Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=-4.5\text{V}, I_{\text{D}}=-5\text{A}$	-	21	31	$\text{m}\Omega$
		$V_{\text{GS}}=-10\text{V}, I_{\text{D}}=-8\text{A}$	-	16	21	$\text{m}\Omega$
Forward Transconductance	$g_{\text{FS}}$	$V_{\text{DS}}=-5\text{V}, I_{\text{D}}=-5\text{A}$	15	-	-	S

**Dynamic Characteristics**

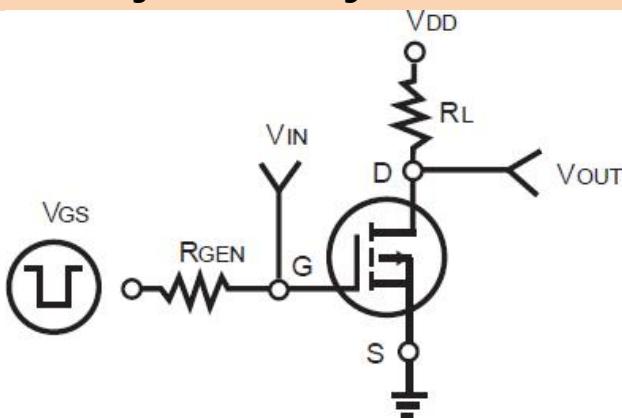
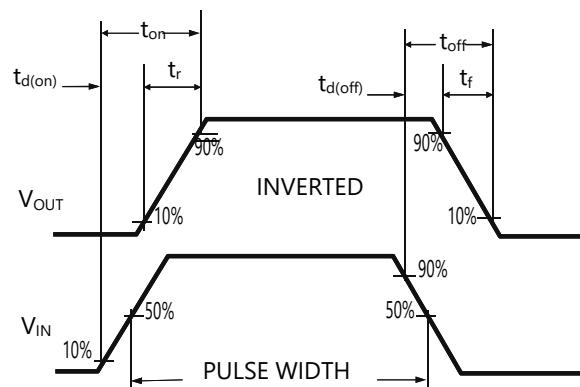
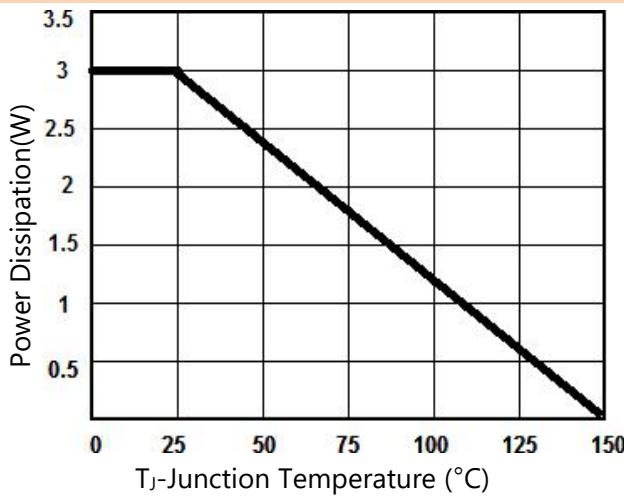
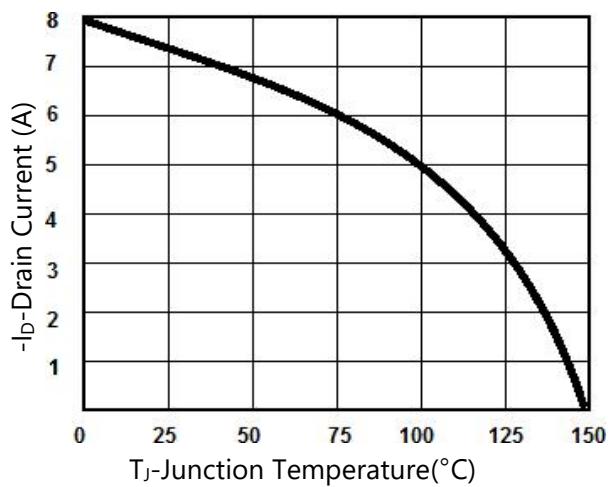
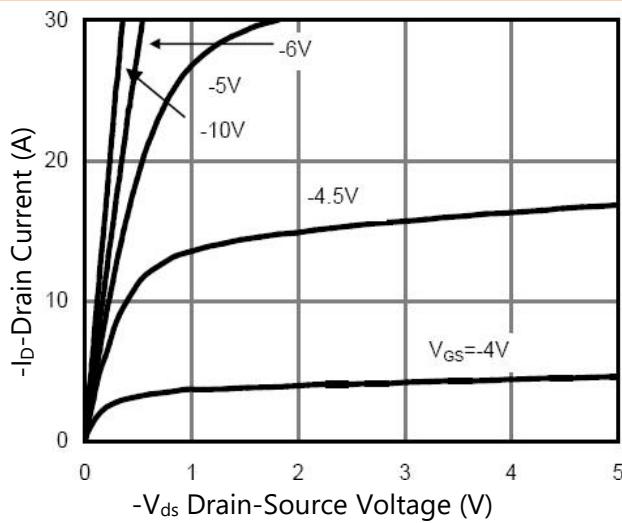
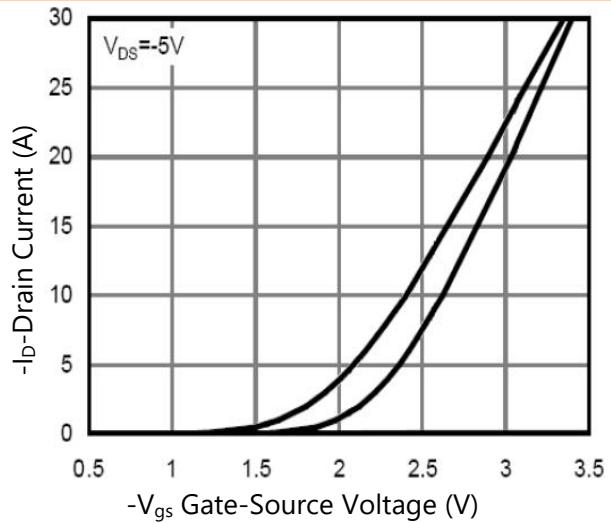
Input Capacitance	$C_{\text{iss}}$	$V_{\text{DS}}=-20\text{V}, V_{\text{GS}}=0\text{V}, F=1.0\text{MHz}$	-	2050	-	pF
Output Capacitance	$C_{\text{oss}}$		-	260	-	pF
Reverse Transfer Capacitance	$C_{\text{rss}}$		-	150	-	pF

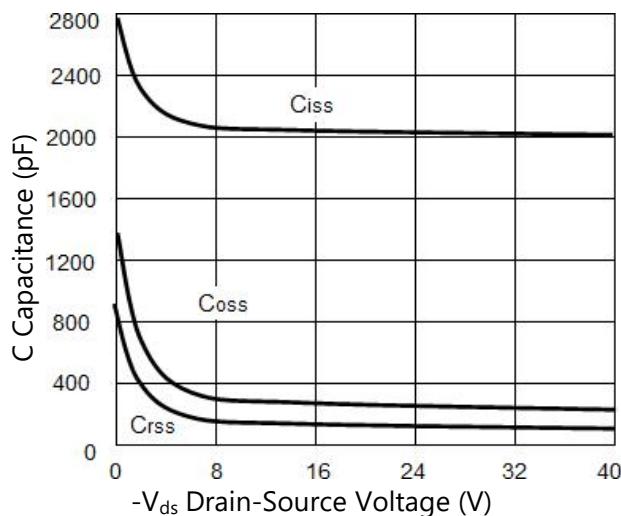
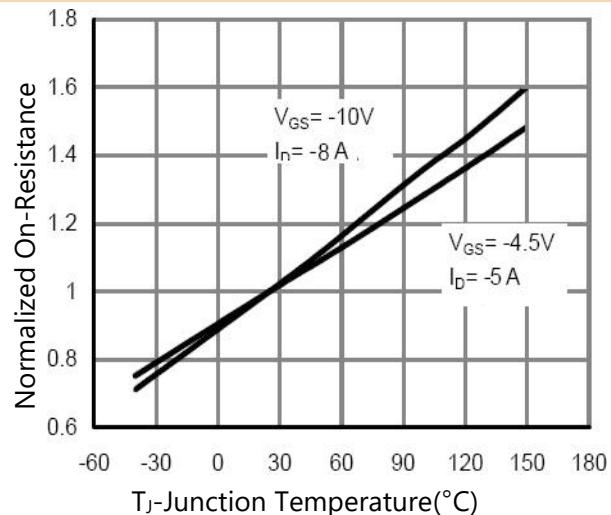
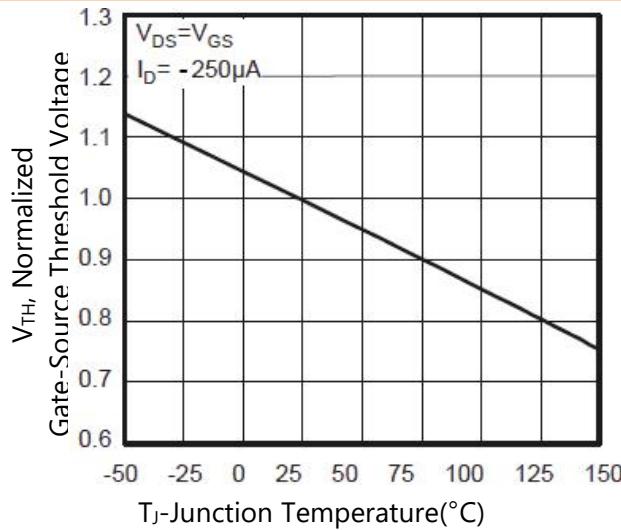
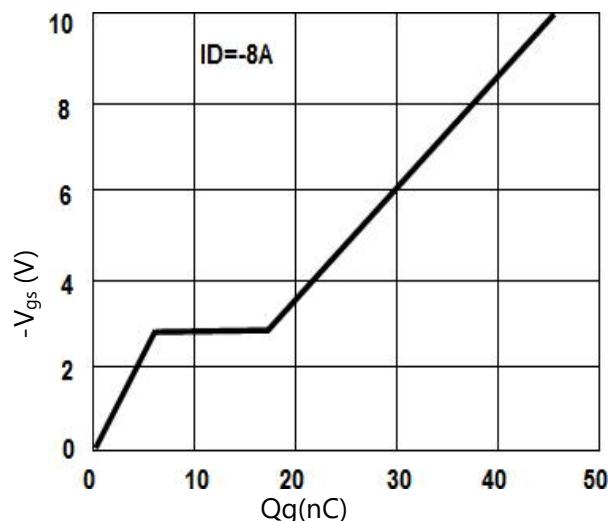
**Switching Characteristics**

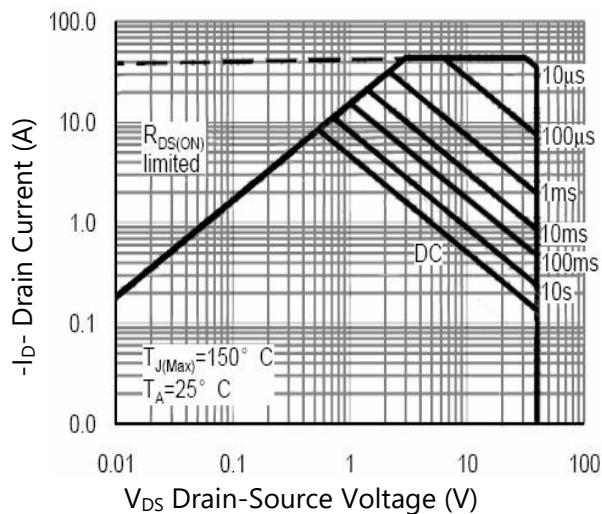
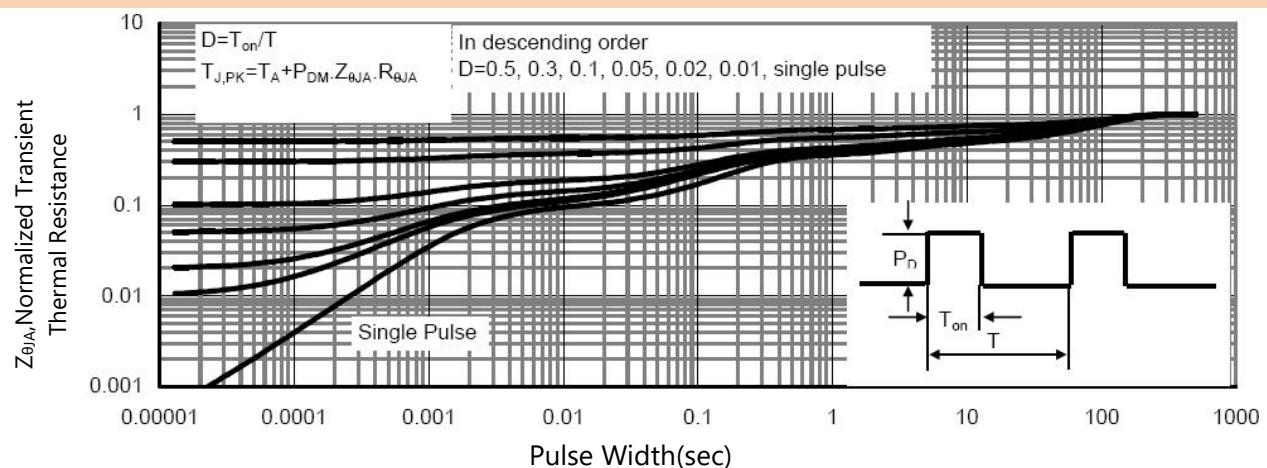
Turn-on Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{DS}}=-20\text{V}, R_{\text{L}}=1.6\Omega, V_{\text{GS}}=-10\text{V}, R_{\text{GEN}}=3\Omega$	-	10	-	nS
Turn-on Rise Time	$t_{\text{r}}$		-	24	-	nS
Turn-Off Delay Time	$t_{\text{d}(\text{off})}$		-	40	-	nS
Turn-Off Fall Time	$t_{\text{f}}$		-	9	-	nS
Total Gate Charge	$Q_{\text{g}}$	$V_{\text{DS}}=-20\text{V}, I_{\text{D}}=-8\text{A}, V_{\text{GS}}=-10\text{V}$	-	45	-	nC
Gate-Source Charge	$Q_{\text{gs}}$		-	6	-	nC
Gate-Drain Charge	$Q_{\text{gd}}$		-	11	-	nC

**Drain-Source Diode Characteristics**

Source-Drain Current(Body Diode)	$I_{\text{SD}}$		-	-	-8	A
Diode Forward Voltage	$V_{\text{SD}}$	$V_{\text{GS}}=0\text{V}, I_{\text{S}}=-1\text{A}$	-	-	-1.2	V

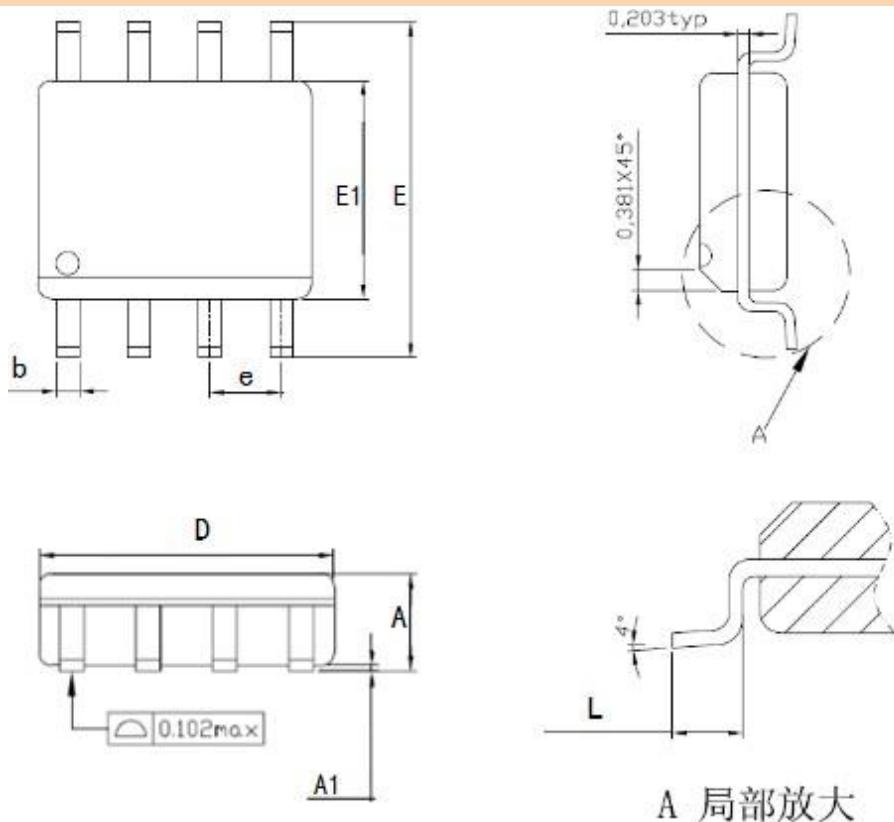

**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**
**Figure 1. Switching Test Circuit**

**Figure 2. Switching Waveform**

**Figure 3. Power Dissipation**

**Figure 4. Drain Current**

**Figure 5. Output Characteristics**

**Figure 6. Transfer Characteristics**



**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**
**Figure 7. Capacitance**

**Figure 8.  $R_{DS(ON)}$  vs Junction Temperature**

**Figure 9.  $V_{GS(th)}$  vs Junction Temperature**

**Figure 10. Gate Charge**



**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**
**Figure 11. Safe Operation Area**

**Figure 12. Normalized Maximum Transient Thermal Impedance**


## PACKAGE INFORMATION

### SOT-8



Symbol	Dimensions In Millimeters		
	Min.	Typ.	Max.
A	1.350	1.550	1.750
A1	0.100	0.150	0.200
b	0.346	0.406	0.466
D	4.800	4.890	4.980
E	5.750	6.000	6.250
E1	3.810	3.900	3.990
e	1.27 TYP.		
L	0.406	0.838	1.270